Markku A Sopanen

List of Publications by Year
in descending order

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53	1,098	567281	414414
papers	citations	15 h-index	32 g-index

53	53	53	976
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Luminescence from excited states in strain-inducedInxGa1â^'xAs quantum dots. Physical Review B, 1995, 51, 13868-13871.	3.2	174
2	Zeeman Effect in Parabolic Quantum Dots. Physical Review Letters, 1996, 77, 342-345.	7.8	99
3	Selective growth of InGaAs on nanoscale InP islands. Applied Physics Letters, 1994, 65, 1662-1664.	3.3	93
4	Strainâ€induced quantum dots by selfâ€organized stressors. Applied Physics Letters, 1995, 66, 2364-2366.	3.3	88
5	Photocatalytic degradation of dyes by CdS microspheres under near UV and blue LED radiation. Separation and Purification Technology, 2013, 120, 206-214.	7.9	72
6	Selfâ€organized InP islands on (100) GaAs by metalorganic vapor phase epitaxy. Applied Physics Letters, 1995, 67, 3768-3770.	3.3	70
7	High Quality GaAs Nanowires Grown on Glass Substrates. Nano Letters, 2012, 12, 1912-1918.	9.1	70
8	Grass-like Alumina with Low Refractive Index for Scalable, Broadband, Omnidirectional Antireflection Coatings on Glass Using Atomic Layer Deposition. ACS Applied Materials & Interfaces, 2017, 9, 15038-15043.	8.0	38
9	Atomic layer etching of gallium nitride (0001). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	37
10	Transformation of Self-Assembled InAs/InP Quantum Dots into Quantum Rings without Capping. Nano Letters, 2005, 5, 1541-1543.	9.1	36
11	Enhanced optical properties of in situ passivated nearâ€surface AlxGa1â^'xAs/GaAs quantum wells. Applied Physics Letters, 1996, 68, 2216-2218.	3.3	32
12	Growth of GaInAsSb using tertiarybutylarsine as arsenic source. Journal of Crystal Growth, 1994, 145, 492-497.	1.5	30
13	Metal Contacts on InN: Proposal for Schottky Contact. Japanese Journal of Applied Physics, 2006, 45, 36-39.	1.5	22
14	Growth of high-quality GaSb by metalorganic vapor phase epitaxy. Journal of Electronic Materials, 1995, 24, 1691-1696.	2.2	20
15	Metalorganic vapor phase epitaxial growth of AlGaSb and AlGaAsSb using all-organometallic sources. Journal of Crystal Growth, 1996, 169, 417-423.	1.5	17
16	Red luminescence from strainâ€induced GaInP quantum dots. Applied Physics Letters, 1996, 69, 3393-3395.	3.3	17
17	Fabrication and photoluminescence of quantum dots induced by strain of self-organized stressors. Solid-State Electronics, 1996, 40, 601-604.	1.4	15
18	InGaN-based 405 nm near-ultraviolet light emitting diodes on pillar patterned sapphire substrates. CrystEngComm, 2010, 12, 3152.	2.6	13

#	Article	IF	Citations
19	Growth and characterization of GaP layers on silicon substrates by metalâ€organic vapour phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1607-1609.	0.8	11
20	Temperature Dependence of Current-Voltage Characteristics of Auâˆ•Ga[sub 0.51]In[sub 0.49]P Schottky Barrier Diodes. AIP Conference Proceedings, 2011, , .	0.4	10
21	Inhomogeneous Barrier Height Analysis of (Ni/Au)â€“InAlGaN/GaN Schottky Barrier Diode. Japanese Journal of Applied Physics, 2011, 50, 030201.	1.5	10
22	Recombination lifetime in InGaN/GaN based light emitting diodes at low current densities by differential carrier lifetime analysis. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 327-331.	0.8	10
23	Fluorescence-enhancing plasmonic silver nanostructures using azopolymer lithography. RSC Advances, 2016, 6, 48129-48136.	3.6	9
24	A technique for large-area position-controlled growth of GaAs nanowire arrays. Nanotechnology, 2016, 27, 135601.	2.6	9
25	Tailoring of Energy Levels in Strain-Induced Quantum Dots. Japanese Journal of Applied Physics, 1999, 38, 1081-1084.	1.5	8
26	InGaAs/InP Quantum Dots Induced by Self-Organized InAs Stressor-Islands. Japanese Journal of Applied Physics, 2005, 44, L518-L520.	1.5	8
27	Tunneling Explanation for the Temperature Dependence of Currentâ€“Voltage Characteristics of Pt/InN Schottky Barrier Diodes. Japanese Journal of Applied Physics, 2009, 48, 070201.	1.5	8
28	Recombination processes in strain-induced InGaAs quantum dots. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1995, 17, 1699-1703.	0.4	7
29	Low energy electron beam induced damage on gallium nitride based materials. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1563-1565.	0.8	7
30	Synchrotron radiation Xâ€ray topography and Xâ€ray diffraction of homoepitaxial GaN grown on ammonothermal GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1630-1632.	0.8	7
31	Nonlinear plasmonic behavior of nanohole arrays in thin gold films for imaging lipids. Applied Physics Letters, 2018, 112, .	3.3	7
32	Effect Of Inp Passivation On Carrier Recombination in InxGa1-xAs/GaAs Surface Quantum Wells. Japanese Journal of Applied Physics, 1999, 38, 1133-1134.	1.5	6
33	Longitudinal Stark Effect in Parabolic Quantum Dots. Japanese Journal of Applied Physics, 2001, 40, 2002-2005.	1.5	6
34	Photoluminescence of buried InGaAs grown on nanoscale InP islands by MOVPE. Journal of Crystal Growth, 1994, 145, 988-989.	1.5	3
35	Fabrication of GaInAs quantum disks using selfâ€organized InP islands as a mask in wet chemical etching. Applied Physics Letters, 1996, 69, 4029-4031.	3.3	3
36	Evolution of Self-Assembled InAs/InP Islands into Quantum Rings. Japanese Journal of Applied Physics, 2005, 44, L1323-L1325.	1.5	3

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37	Thermally assisted recovery of low energy electron beam irradiation induced optical degradation of GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 461-463.	0.8	3
38	Praseodymium Dioxide Doping of In1â^'xGaxAsyP1â^'y Epilayer Grown with Liquid Phase Epitaxy. Materials Research Society Symposia Proceedings, 1993, 301, 27.	0.1	2
39	Highly Tunable Emission from Strain-Induced InGaAsP/InP Quantum Dots. Japanese Journal of Applied Physics, 2005, 44, L976-L978.	1.5	2
40	Forward Bias Capacitance-Voltage Measurements on Semiconductors Using Co-Planar Ohmic and Schottky Contacts in a Cylindrical Geometry. Journal of Nano Research, 2010, 12, 45-54.	0.8	2
41	GaAs Nanowire and Crystallite Growth on Amorphous Substrate from Metalorganic Precursors. Japanese Journal of Applied Physics, 2010, 49, 020213.	1.5	2
42	Nonlinear dynamics of non-equilibrium holes in p-type modulation-doped GaInNAs/GaAs quantum wells. Nanoscale Research Letters, 2011, 6, 191.	5.7	2
43	Analysis of Dislocations Generated during Metalâ€“Organic Vapor Phase Epitaxy of GaN on Patterned Templates. Japanese Journal of Applied Physics, 2013, 52, 01AF01.	1.5	2
44	Metalorganic vapor phase epitaxy of wurtzite InP nanowires on GaN. Applied Physics Letters, 2020, 116, 093101.	3.3	2
45	Fabrication of nanostructures using MBE and MOVPE. Physica Scripta, 1994, T54, 241-243.	2.5	1
46	Optical properties of self-organized InGaAs/InP dots. , 0, , .		1
47	Recent progress towards acoustically mediated carrier injection into individual nanostructures for single photon generation. Proceedings of SPIE, 2010, , .	0.8	1
48	Defect studies with positrons: What could we learn on III-nitride heterostructures?. Journal of Physics: Conference Series, 2010, 225, 012057.	0.4	1
49	Temperature Dependence Of Current-Voltage Characteristics Of Auâ^•p-GaAsN Schottky Barrier Diodes, With Small N Content. , 2011, , .		1
50	Effect of atomic-layer-deposited AlN on near-surface InGaAs/GaAs structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1560-1562.	0.8	1
51	Carrier Dynamics in Strain Induced Quantum Dots Modeled by Rate Equations and Gaussian Excitation Beam Distribution. Japanese Journal of Applied Physics, 2008, 47, 5499-5502.	1.5	0
52	Band-Edge Luminescence Degradation by Low Energy Electron Beam Irradiation in GaN Grown by Metalâ€“Organic Vapor Phase Epitaxy in H2and N2Ambients. Japanese Journal of Applied Physics, 2013, 52, 11NH04.	1.5	0
53	Optical degradation and defect activation in MOVPE grown near surface InGaN quantum wells under low energy electron beam irradiation. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 806-809.	0.8	0